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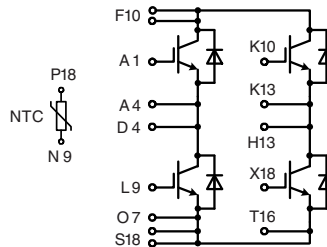


# IGBT Modules in ECO-PAC 2

H-Bridge configuration

Short Circuit SOA Capability  
Square RBSOA

$I_{C25} = 69 \text{ A}$   
 $V_{CES} = 600 \text{ V}$   
 $V_{CE(sat) \text{ typ.}} = 2.3 \text{ V}$



Pin arrangement see outlines

IGBTs		
Symbol	Conditions	Maximum Ratings
$V_{CES}$	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	600 V
$V_{GES}$		$\pm 20$ V
$I_{C25}$	$T_C = 25^{\circ}\text{C}$	69 A
$I_{C80}$	$T_C = 80^{\circ}\text{C}$	48 A
$I_{CM}$ $V_{CEK}$	$V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	100 A
$t_{SC}$ (SCSOA)		$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 22 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive
$P_{tot}$	$T_C = 25^{\circ}\text{C}$	208 W

Symbol	Conditions	Characteristic Values ( $T_{VJ} = 25^{\circ}\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 75 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.3 2.8	2.8 V V	
$V_{GE(th)}$	$I_C = 1 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
$I_{CES}$	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			0.8 mA 4.4 mA	
$I_{GES}$	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			100 nA	
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$ $E_{on}$ $E_{off}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 300 \text{ V}; I_C = 40 \text{ A}$ $V_{GE} = 15/0 \text{ V}; R_G = 22 \Omega$		50 55 300 30	ns ns ns ns	
			1.8 1.4	mJ mJ	
$C_{ies}$		$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		2.8	nF
$R_{thJC}$ $R_{thJH}$		(per IGBT) with heatsink compound (0.42 K/m.K; 50 $\mu\text{m}$ )		1.2	0.6 K/W K/W

### Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- ultra fast free wheeling diodes
- solderable pins for PCB mounting
- package with copper base plate

### Advantages

- space savings
- reduced protection circuits
- package designed for wave soldering

### Typical Applications

- motor control
  - DC motor armature winding
  - DC motor excitation winding
  - synchronous motor excitation winding
- supply of transformer primary winding
  - power supplies
  - welding
  - X-ray
  - UPS
  - battery charger

**Reverse diodes (FRED)**

Symbol	Conditions	Maximum Ratings	
$I_{F25}$	$T_C = 25^\circ\text{C}$	56	A
$I_{F80}$	$T_C = 80^\circ\text{C}$	35	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 40\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.32	2.59	V
		1.58		V
$I_{RM}$ $t_{rr}$	$I_F = 30\text{ A}; di_F/dt = 500\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 300\text{ V}; V_{GE} = 0\text{ V}$	70	15	A
			ns	
$R_{thJC}$ $R_{thJH}$	with heatsink compound (0.42 K/m.K; 50 $\mu\text{m}$ )		1.3	KW
		2.6		KW

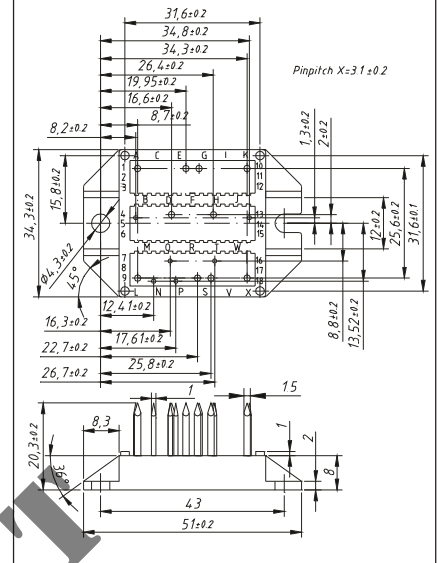
**Temperature Sensor NTC**

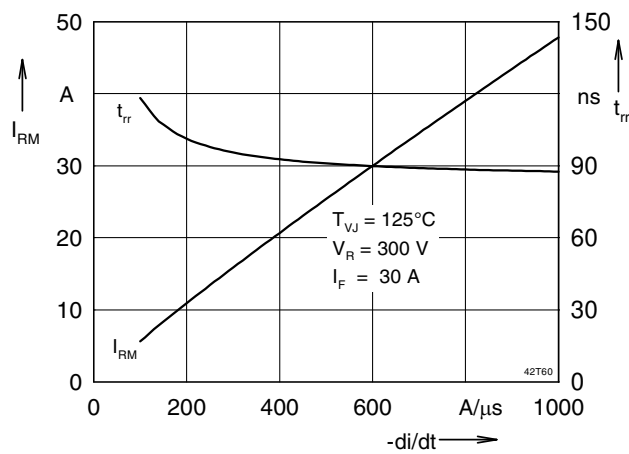
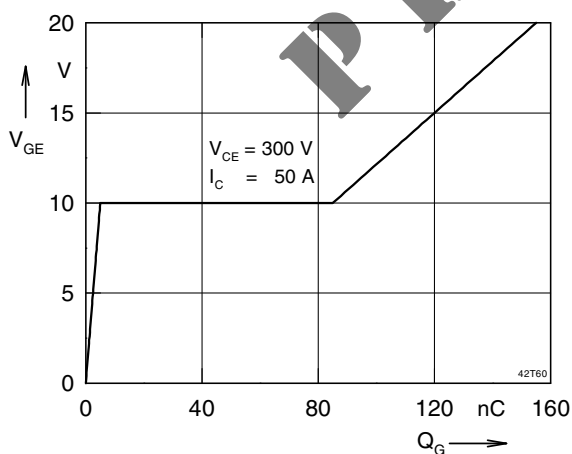
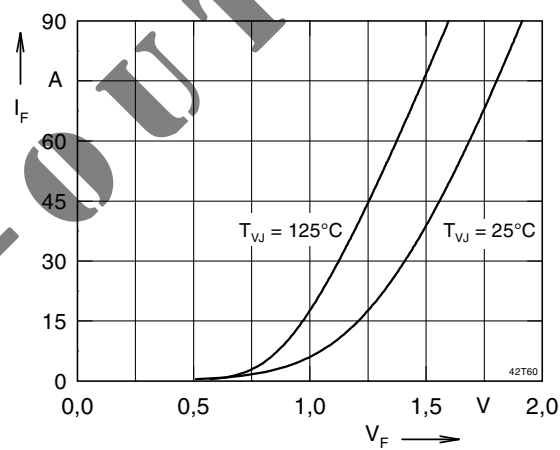
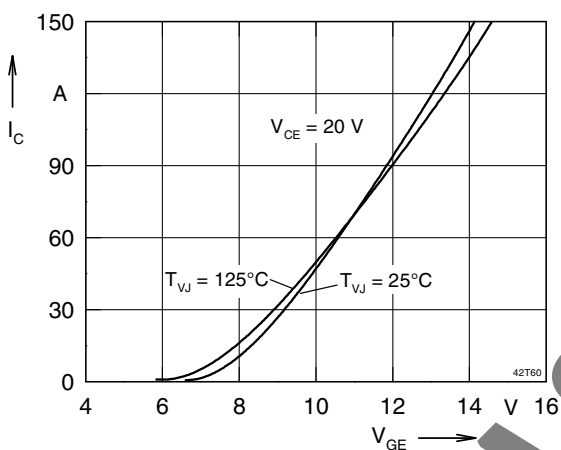
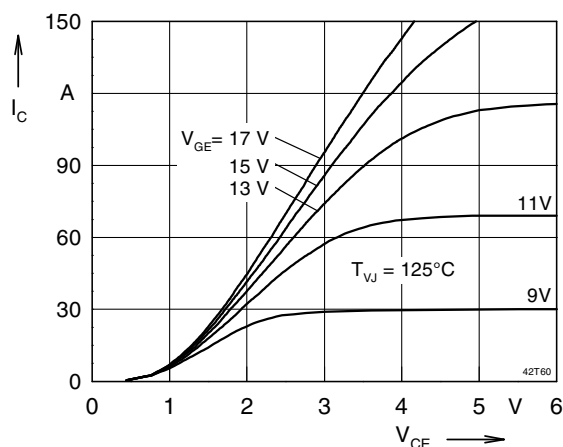
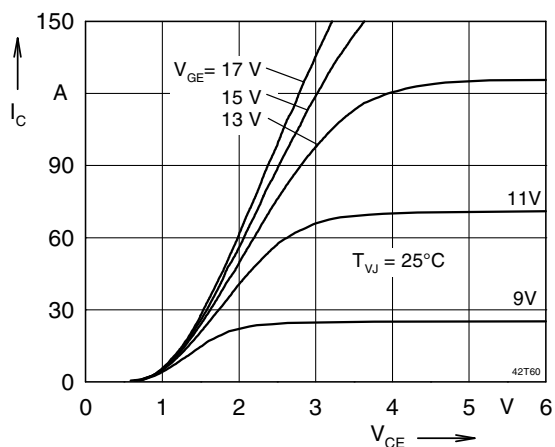
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{25}$ $B_{25/50}$	$T = 25^\circ\text{C}$	455	470	485 k $\Omega$
			3474	K

**Module**

Symbol	Conditions	Maximum Ratings	
$T_{VJ}$		-40...+150	$^\circ\text{C}$
$T_{stg}$		-40...+150	$^\circ\text{C}$
$V_{ISOL}$	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	8000	V~
$M_d$	mounting torque (M4)	1.5 - 2.0	Nm
		14 - 18	lb.in.
$a$	Max. allowable acceleration	50	$\text{m/s}^2$

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$d_s$	Creepage distance on surface (Pin to heatsink)	11.2		mm
$d_A$	Strike distance in air (Pin to heatsink)	11.2		mm
<b>Weight</b>		24		g

**Dimensions in mm (1 mm = 0.0394")**




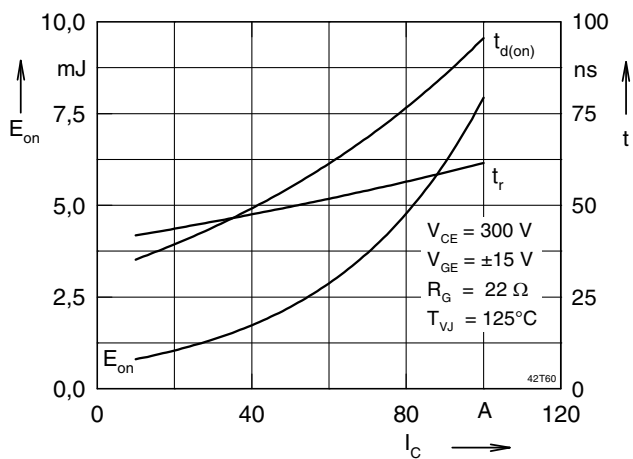


Fig. 7 Typ. turn on energy and switching

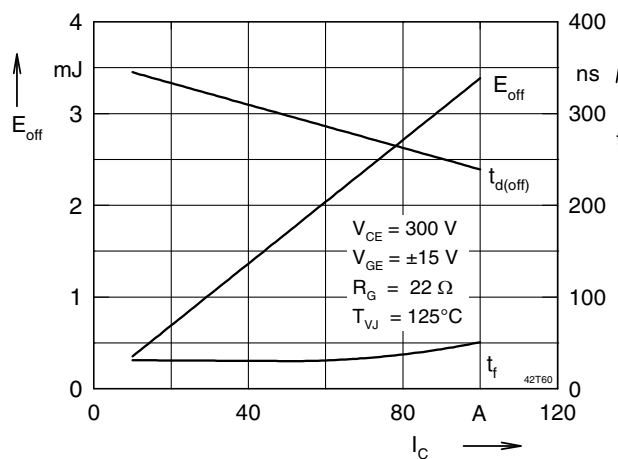


Fig. 8 Typ. turn off energy and switching times versus collector current

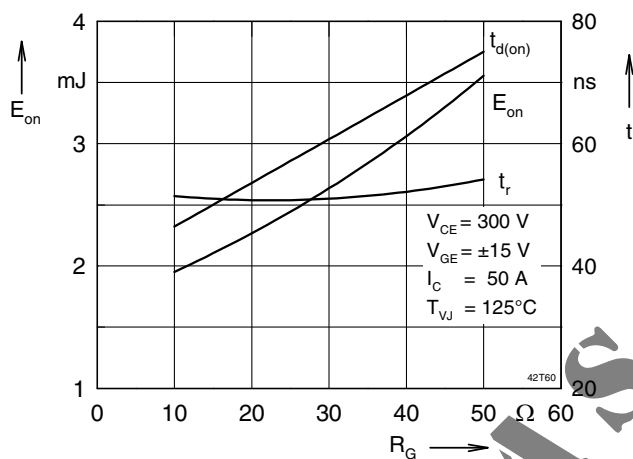


Fig. 9 Typ. turn on energy and switching

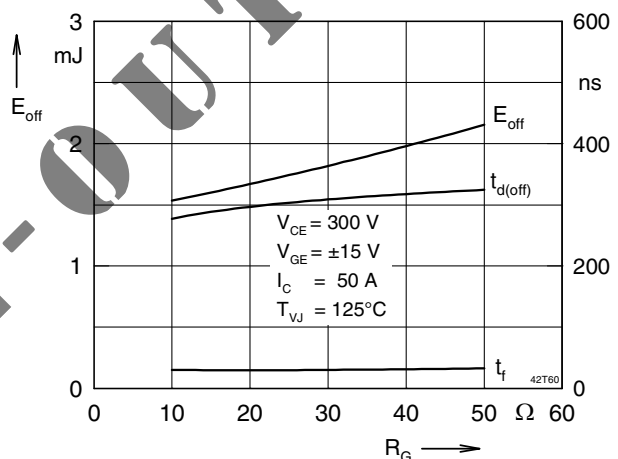


Fig. 10 Typ. turn off energy and switching times versus gate resistor

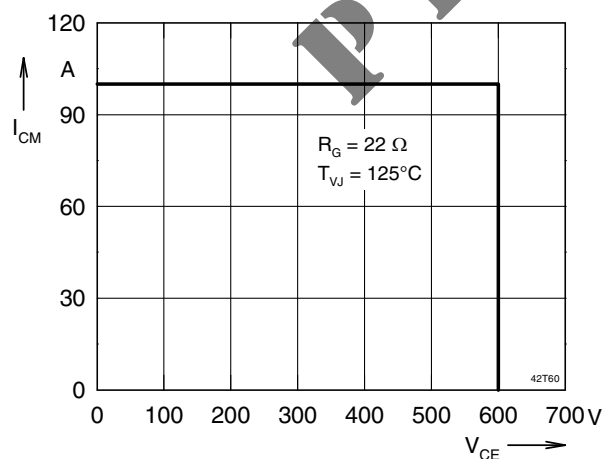


Fig. 11 Reverse biased safe operating area

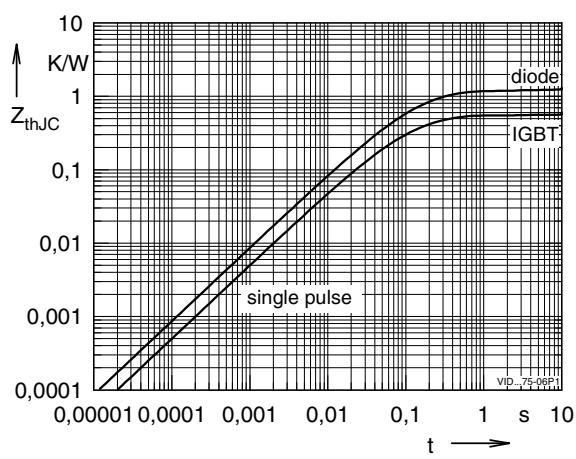


Fig. 12 Typ. transient thermal impedance RBSOA